

# **High Isolation SPDT Switch** DC to 15 GHz Die

ADH232S

#### 1.0 **SCOPE**

This specification documents the detail requirements for space qualified die per MIL-PRF-38534 class K except as modified herein.

The manufacturing flow described in the SPACE DIE BROCHURE is to be considered a part of this specification.

This datasheet specifically details the space grade version of this product. A more detailed operational description and a complete datasheet for commercial product grades can be found at www.analog.com/HMC232

2.0 Part Number. The complete part number(s) of this specification follow:

> Part Number Description

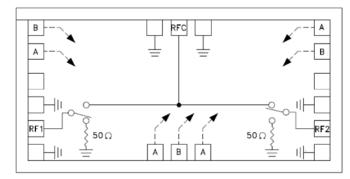
DC-15GHz High Isolation SPDT Switch Die HMC8800

#### 3.0 **Die Information**

#### 3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad and Backside Metalization
41 mil x 81 mil	4 mil ± 0.5 mil	Au

#### 3.2 Die Picture



Control Input		Signal Path State			
Α	В	RFC to RF1	RFC to RF2		
High	Low	ON	OFF		
Low	High	OFF	ON		

Caution: Do not "Hot Switch" power levels greater than +26 dBm (VCTL = 0/-5 VDC)

- RF1\*
- A\*\*
- B\*\*
- RFC\*
- A\*\*
- B\*\*
- RF2\*
- A\*\*
- B\*\* 9.
- 10. A\*\*
- Die bottom must be connected to RF
- No connection required for unlabeled pads
- \* (DC coupled, matched to 50 ohms, blocking cap required if RF line potential not equal to 0V)
- \*\* Using any one of the A and any one of the B Pads connection is acceptable

ASD0016558 Rev. D

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### 3.3 Absolute Maximum Ratings 1/

RF Input Power (Vctl = -5V) (0.5 – 15GHz)	+30dBm (@ +50°C)
Control Voltage Range (A & B)	+1 V to -7.5 Vdc
Channel Temperature	150°C
Thermal resistance	92°C/W
Storage Temperature	65°C to +150°C
Operating Temperature	55°C to +85°C
ESD Sensitivity (HBM)	

Absolute Maximum Ratings Notes:

#### 4.0 <u>Die Qualification</u>

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Pre-screen test post assembly required prior to die qualification, to remove all assembly related rejects.
- (b) Mechanical Shock or Constant Acceleration not performed; die qualification is performed in an open carrier.
- (c) Interim and post burn-in electrical tests will include static tests screened at +25°C only.

Table I - Dice Electrical Characteristics						
Parameter	Symbol	Conditions 1/, <u>2</u> /, <u>3</u> /, <u>4</u> / 50 Ω System	Limit Min	Limit Max	Units	
Insertion Loss	IL	DC – 6 GHz DC – 10 GHz DC – 15 GHz		1.6 2.2 2.9	dB	
Isolation	Iso	DC – 6 GHz DC – 10 GHz DC – 15 GHz	50 45 40		dB	
Return Loss "On State"	S11(on)	DC – 6 GHz DC – 15 GHz	17 9		dB	
Return Loss RF1, RF2 "Off State"	S11(off)	DC – 6 GHz DC – 15 GHz	12 9		dB	
Input Power for 1dB Compression	IP1dB	0.5 – 15 GHz	21		dBm	

### Table I Notes:

- 1/ Limits apply at +25°C only.
- <u>2/</u> Tested with VCTLA/B Low = -0.2V, High = -5V
- 3/ S-par data to be tabulated at 50MHz and every 1GHz, 1GHz to 15GHz. Pin = -25dBm
- 4/ P1dB shall be measured at 5GHz, 10GHz, 15GHz, Go-No-Go

<sup>1/</sup> Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

Table II - Electrical Characteristics for Qualification Samples							
Parameter	Symbol	Conditions $1/$ , $2/$ , $3/$ , $4/$ , $5/$ , $6/$ -40C $\leq$ T <sub>A</sub> $\leq$ 85°C, 50 ohm system unless otherwise specified	Sub- groups	Min Limit	Max Limit	Units	
		DC – 6.0 GHz	4		1.6		
		3 3 3 3 3 3 3	5,6		1.7		
Insertion Loss	IL	DC – 10.0 GHz	4		2.2	dB	
			5,6		2.3		
		DC – 15.0 GHz	4		2.9		
			5,6		3.0		
		DC – 6.0 GHz	4,5,6	55			
Isolation	ISO	DC – 10.0 GHz	4,5,6	50		dB	
		DC – 15.0 GHz	4,5,6	45			
		DC 60611-	4	18			
Return Loss "On State"	RL(on)	DC – 6.0 GHz	5,6	17		dB	
		DC – 15.0 GHz	4,5,6	12			
Return Loss RF1, RF2, "Off	RL(off)	DC - 6.0 GHz	4,5,6	14		dB	
State"	KL(OII)	DC – 15.0 GHz	4,5,6	12		ав	
Input Power for 1dB Compression	IP1dB	0.5 – 15.0 GHz	4,5,6	21		dBm	
Input Third Order Intercept (Two-Tone $P_{IN} = 7$ dBm each tone, 1MHz Separation)	IIP3	0.5 – 15.0 GHz	4,5,6	42		dBm	

#### Table II Notes:

- Pre burn-in and Post burn-in electrical require S-parameter testing only as defined. Final electrical tests shall incorporate power tests as defined.
- Temperature testing required for Final Electrical testing only Tested with VCTLA/B Low = -0.2 V, High = -5 V
- S-par data to be tabulated at 50Hz and every 1 GHz, 1 GHz to 15 GHz. Pin = -25 dBm P1dB shall be measured at 1 GHz to 15 GHz, 2 GHz steps
- IP3 shall be measured at 1 GHz to 15GHz, 2 GHz steps

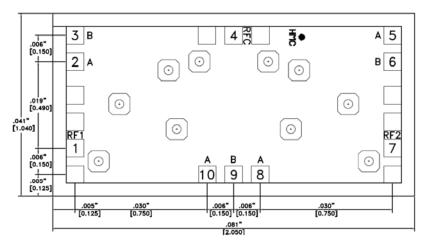
Table III - Endpoint and Delta Limits (+25°C)								
(Product is tested in accordance with Table II with the following exceptions)								
Dawa wa a ta w		Sub-	End-point		End-point Dolta Units			
	Symbol				Dalta	l linite		
Parameter	Symbol	groups	Min	Max	Delta	Units		

### Table III Notes:

- 1/Table II limits will not be exceeded
- $\frac{1}{2}$ / 240 hour burn in and Group C end point electrical parameters. Deltas are performed at T<sub>A</sub> = 25°C

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## 5.0 <u>Die Outline</u>



#### NOTES:

- 1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
- 2. BOND PADS ARE 0.004" SQUARE
- 3. TYPICAL BOND PAD SPACING CENTER TO CENTER IS .006"
- 4. BACKSIDE METALIZATION: GOLD
- 5. BOND PAD METALIZATION: GOLD
- 6. BACKSIDE OF DIE IS GROUND
- 7. DIE THICKNESS IS .004"
- 8. NO CONNECTION REQUIRED FOR UNLABLED BOND PADS

- 1. RF1\*
- 2. A\*\*
- 3. B\*\*
- 4. RFC\*
- 5. A\*\*
- 6. B\*\*
- 7. RF2\*
- 8. A\*\*
- 9. B\*\*
- 10. A\*\*
- Die bottom must be connected to RF ground
- No connection required for unlabeled pads
- \* (DC coupled, matched to 50 ohms, blocking cap required if RF line potential not equal to 0V)
- \*\* Using any one of the A and any one of the B Pads connection is acceptable

Rev	Description of Change	Date
Α	Initiate	27-October-2015
В	Changes to Section 3.2 (Absolute Maximum Ratings) and added clarification to sections 3.3 and 5.0	12-December- 2015
С	Corrected minimum operating temperature from -40°C to -55°C, and corrected maximum operating temperature from 80°C to 85°C, corrected IP3 test conditions and notes in Table II, corrected numbering in Die Outline pin descriptions	26-February-2018
D	Add note to exceptions list clarifying test temperatures for interim and post burn-in electrical tests	4-June-2019

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